

# **ELECTRICAL SPECIFICATIONS (Tcase = 25°C)**

# **STATIC**

(off)

Symbol	Test Conditions	Value			Unit
	rest Conditions		Тур.	Max.	)
BVCEO	Collector-Emitter Sustaining Voltage (IC = 3.0 mAdc, IB = 0)	12	-	-	Vdc
BVCBO	Collector-Base Breakdown Voltage (IC=1.0 Adc, IE=0)	20	-	-	Vdc
BVEBO	Emitter Base Breakdown Voltage (IE = 0.01 mAdc, IC = 0)	2.5	-	-	Vdc
ICBO	Collector Cutoff Current (VCB = 15 Vdc, IE = 0)	-	-	.02	mA

(on)

HFE	DC Current Gain (IC = 3.0 mAdc, VCE = 1.0 Vdc)	25	-	250	-
VBE(sat)	Base-Emitter Saturation Voltage (IC = 10 mAdc, IB = 1.0 mAdc)	-	-	1.0	Vdc
VCE(sat)	Collector-Emitter Saturation Voltage (IC = 10 mAdc, IB = 1.0 mAdc)	-	-	0.4	Vdc

# **DYNAMIC**

Symbol	Test Conditions	Value			Unit
	rest conditions		Тур.	Max.	Offic
f <sub>⊤</sub>	Current-Gain - Bandwidth Product (IC = 5.0 mAdc, VCE = 6 Vdc, f = 100 MHz)	900	1500	-	MHz
ССВ	Collector-base Capacitance (VCB = 10 Vdc, IE = 0, f = 1.0 MHz)	-	-	1.0	pF

#### **FUNCTIONAL**

Symbol	Test Conditions			Value		
Symbol Test Conditions		Min.	Тур.	Max.	Unit	
NF	Noise Figure (figure 1)	IC = 1.5 mAdc, VCE = 6.0 Vdc, f = 200 MHz	-	-	4.5	dB
GPE	Common-Emitter Amplifier Power Gain (figure 1)	IC = 1.5 mAdc, VCE = 6.0 Vdc, f = 200 MHz	20	-	-	dB

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0.25" L, 0.5" Dia. Position 1/4"

from L2

## **FUNCTIONAL (CONT)**

Symbol	Test Conditions		Value			Unit
	Test Co	Min.	Тур.	Max.	Offic	
GU <sub>MAX</sub>	Maximum Unilateral Gain (1)	IC = 5 mAdc, VCE = 6.0 Vdc, f = 200 MHz	-	17	-	dB
MAG	Maximum Available Gain	IC = 5 mAdc, VCE = 6.0 Vdc, f = 200 MHz	-	18	-	dB
S <sub>21</sub>   <sup>2</sup>	Insertion Gain	IC = 5 mAdc, VCE = 6.0 Vdc, f = 200 MHz	-	12	-	dB

Note: 1. Maximum Unilateral Gain =  $|^{S}21|^{2}$  /  $(1 - |^{S}11|^{2})(1 - |^{S}22|^{2})$ 

Cbypass:

R1:

#### **TEST CIRCUIT SCHEMATIC**

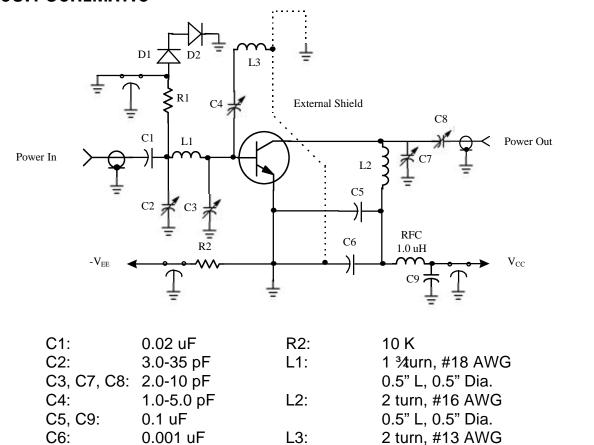


Figure 1. 200 MHz Amplifier for Power Gain and Noise Figure specifications.

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1200 pF

91 ohm

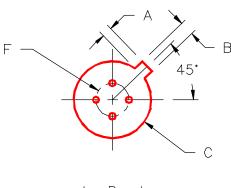


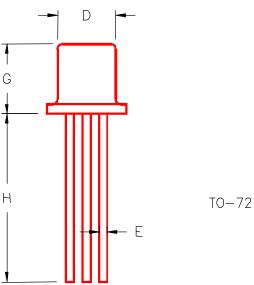
Table 1. Common Emitter S-Parameters, @ VCE = 6 V, IC = 5 mA

f \$11		I	S21		S12		S22	
(MHz)	S11	∠ φ	S21	∠ φ	S12	∠ <b>¢</b>	S22	∠ <b>¢</b>
100	.471	-90	6.78	122	.023	64	.844	-51
200	.314	-145	4.20	100	.034	58	.780	-93
300	.230	156	2.76	91	.043	65	.768	-134
400	.171	108	2.17	86	.056	63	.756	-177
500	.168	54	1.86	79	.062	62	.741	140
600	.149	-9	1.53	71	.069	66	.740	98
700	.137	-72	1.31	67	.073	71	.739	54
800	.119	-129	1.18	64	.092	74	.744	8
900	.153	-174	1.13	58	.101	68	.742	-38
1000	.171	122	.979	49	.106	71	.749	-82



#### PACKAGE STYLE M244





	MINIMUM	MAXIMUM		MINIMUM	MAXIMUM
	INCHES/MM	INCHES/MM		INCHES/MM	INCHES/MM
Α	.020/0,51	.048/1,22			
В	.036/0,91	.046/1,17			
С	.209/5,31	.230/5,84			
D	.178/4,52	.195/4,95			
E	.016/0,41	.020/0,51			
F	.100/2,54				
G	.170/4,32	.210/5,33			
Н	.500/12,70				

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